

KSC2331

Low Frequency Amplifier & Medium Speed Switching

- Complement to KSA931
- High Collector-Base Voltage : V_{CBO}=80V
- Collector Current : I_C=700mA
- Collector Dissipation : P_C=1W



1. Emitter 2. Collector 3. Base

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a =25°C unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|------------------|-----------------------------|-----------|-------|
| V _{CBO} | Collector-Base Voltage | 80 | V |
| V_{CEO} | Collector-Emitter Voltage | 60 | V |
| V _{EBO} | Emitter-Base Voltage | 8 | V |
| I _C | Collector Current | 700 | mA |
| P _C | Collector Power Dissipation | 1 | W |
| TJ | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | -55 ~ 150 | °C |

Electrical Characteristics T_a=25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|---|------|------|------|-------|
| BV _{CBO} | Collector-Base Breakdown Voltage | $I_C=100\mu A, I_E=0$ | 80 | | | V |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | I _C =10mA, I _B =0 | 60 | | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | $I_{E}=10\mu A, I_{C}=0$ | 8 | | | V |
| I _{CBO} | Collector Cut-off Current | V_{CB} =60V, I_{E} =0 | | | 0.1 | μΑ |
| I _{EBO} | Emitter Cut-off Current | V_{EB} =5V, I_C =0 | | | 0.1 | μΑ |
| h _{FE} | DC Current Gain | V_{CE} =2V, I_{C} =50mA | 40 | | 240 | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C =500mA, I _B =50mA | | 0.2 | 0.7 | V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | I _C =500mA, I _B =50mA | | 0.86 | 1.20 | V |
| f _T | Current Gain Bandwidth Product | V _{CE} =10V, I _C =50mA | 30 | 50 | | MHz |
| C _{ob} | Output Capacitance | V _{CB} =10V, I _E =0, f=1MHz | | 8 | | pF |

h_{FE} Classification

| Classification | R | 0 | Y |
|-----------------|---------|----------|-----------|
| h _{FE} | 40 ~ 80 | 70 ~ 140 | 120 ~ 240 |

Typical Characteristics

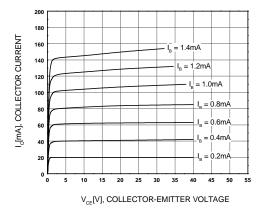


Figure 1. Static Characteristic

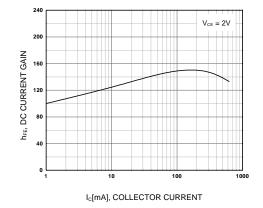


Figure 2. DC current Gain

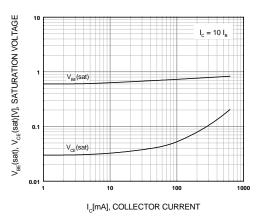


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

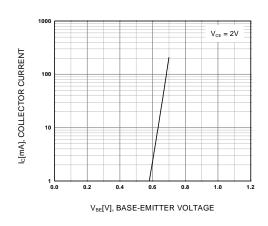


Figure 4. Base-Emitter On Voltage

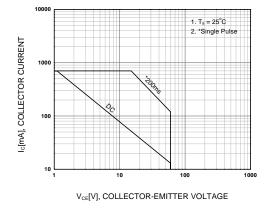


Figure 5. Safe Operating Area

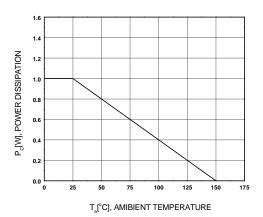
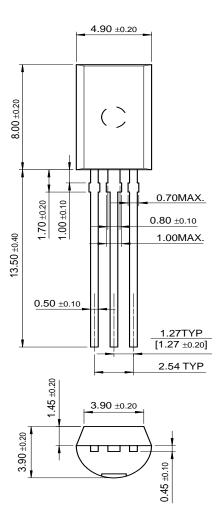


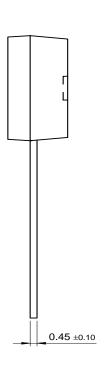
Figure 6. Power Derating

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Package Dimensions

TO-92L





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